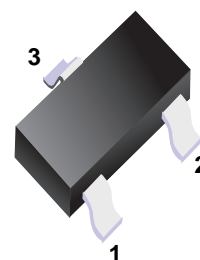


NPN Transistor

■ Features

- Collector Current Capability $I_c=0.2A$
- Collector Emitter Voltage $V_{CE0}=40V$



- 1.Base
- 2.Emitter
- 3.Collector

■ Simplified outline(SOT-323)

■ Marking

| | |
|---------|-----|
| Marking | K2N |
|---------|-----|

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit |
|---|-----------------|------------|---------------|
| Collector - Base Voltage | V_{CB0} | 60 | V |
| Collector - Emitter Voltage | V_{CE0} | 40 | |
| Emitter - Base Voltage | V_{EB0} | 5 | |
| Collector Current - Continuous | I_c | 200 | mA |
| Collector Power Dissipation | P_c | 200 | mW |
| Thermal Resistance From Junction To Ambient | $R_{\theta JA}$ | 625 | $^{\circ}C/W$ |
| Junction Temperature | T_J | 150 | $^{\circ}C$ |
| Storage Temperature Range | T_{stg} | -55 to 150 | |

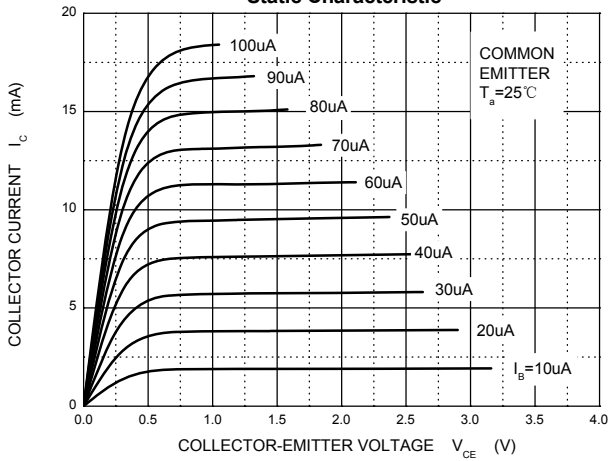
■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|----------------------|--|---|-----|------|------|
| Collector- base breakdown voltage | V _{CBO} | I _c = 100 μA, I _E = 0 (Note.1) | 60 | | | V |
| Collector- emitter breakdown voltage | V _{CEO} | I _c = 1 mA, I _B = 0 (Note.1) | 40 | | | |
| Emitter - base breakdown voltage | V _{EB0} | I _E = 100 μA, I _c = 0 (Note.1) | 5 | | | |
| Collector-base cut-off current | I _{CBO} | V _{CB} = 60 V, I _E = 0 (Note.1) | | | 60 | nA |
| Collector- emitter cut-off current | I _{CEO} | V _{CE} = 40 V, I _E = 0 (Note.1) | | | 700 | |
| Collector- emitter cut-off current | I _{CEx} | V _{CE} = 30 V, V _{BE(off)} = 3V | | | 50 | |
| Emitter cut-off current | I _{EBO} | V _{EB} = 5V, I _c =0 | | | 100 | |
| Collector-emitter saturation voltage (Note.1) | V _{CE(sat)} | I _c =10 mA, I _B =1 mA | | | 0.25 | V |
| | | I _c =50 mA, I _B =5 mA | | | 0.3 | |
| Base - emitter saturation voltage (Note.1) | V _{BE(sat)} | I _c =10 mA, I _B =1 mA | | | 0.85 | |
| | | I _c =50 mA, I _B =5 mA | | | 0.95 | |
| DC current gain (Note.1) | h _{FE(1)} | V _{CE} = 1V, I _c = 100 μA | 40 | | | |
| | h _{FE(2)} | V _{CE} = 1V, I _c = 1 mA | 70 | | | |
| | h _{FE(3)} | V _{CE} = 1V, I _c = 10 mA | 100 | | 300 | |
| | h _{FE(4)} | V _{CE} = 1V, I _c = 50 mA | 60 | | | |
| Delay time | t _d | V _{CC} =3V, V _{BE(off)} =0.5V I _c =10mA, I _{B1} =1mA | | | 35 | nS |
| Rise time | t _r | | | | 35 | |
| Storage time | t _s | | | | 225 | |
| Fall time | t _f | | V _{CC} =3V, I _c =10mA, I _{B1} = I _{B2} =1mA | | | |
| Collector input capacitance | C _{ib} | V _{EB} = 0.5V, I _E = 0, f=1MHz | | | 8 | pF |
| Collector output capacitance | C _{ob} | V _{CB} = 5V, I _E = 0, f=1MHz | | | 4 | |
| Transition frequency | f _T | V _{CE} = 20V, I _c = 10mA, f=100MHz | 300 | | | MHz |

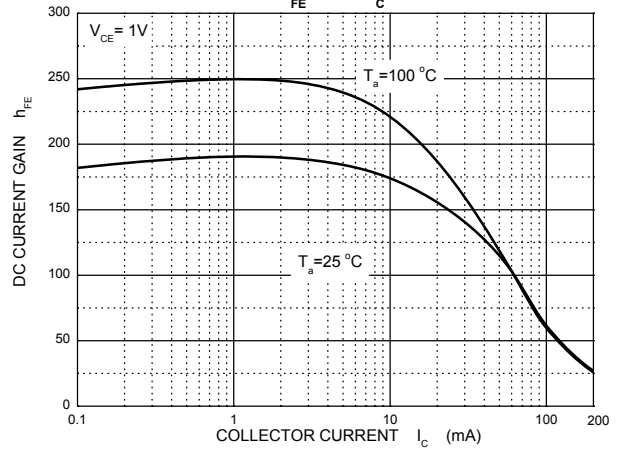
Note.1: Pulse test: pulse width ≤300μs, duty cycle ≤ 2.0%.

■ Typical Characteristics

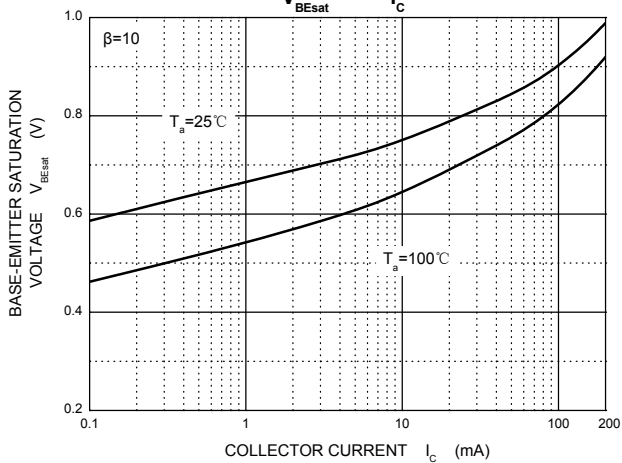
Static Characteristic



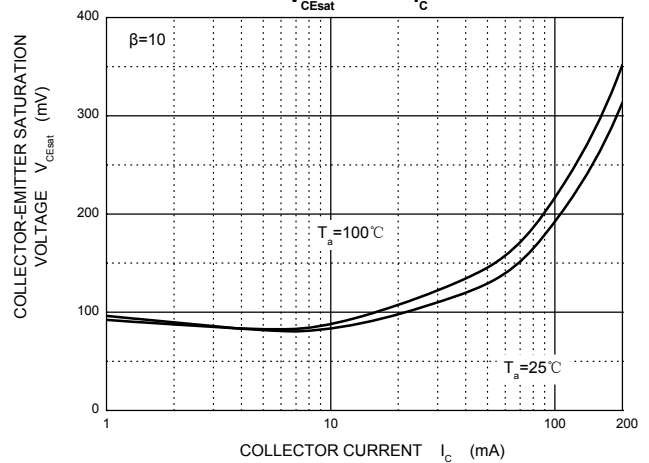
$h_{FE} - I_c$



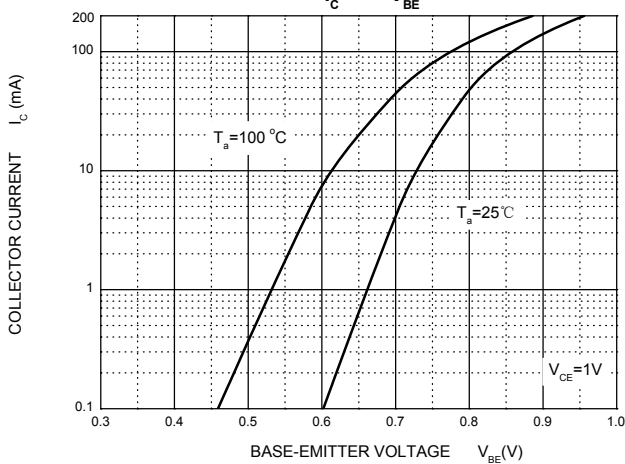
$V_{BEsat} - I_c$



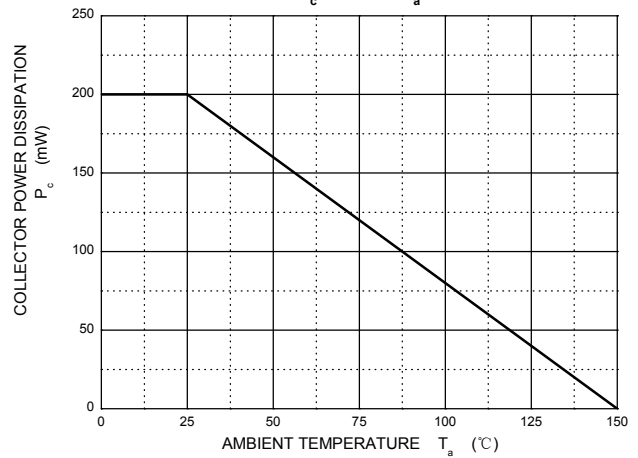
$V_{CEsat} - I_c$



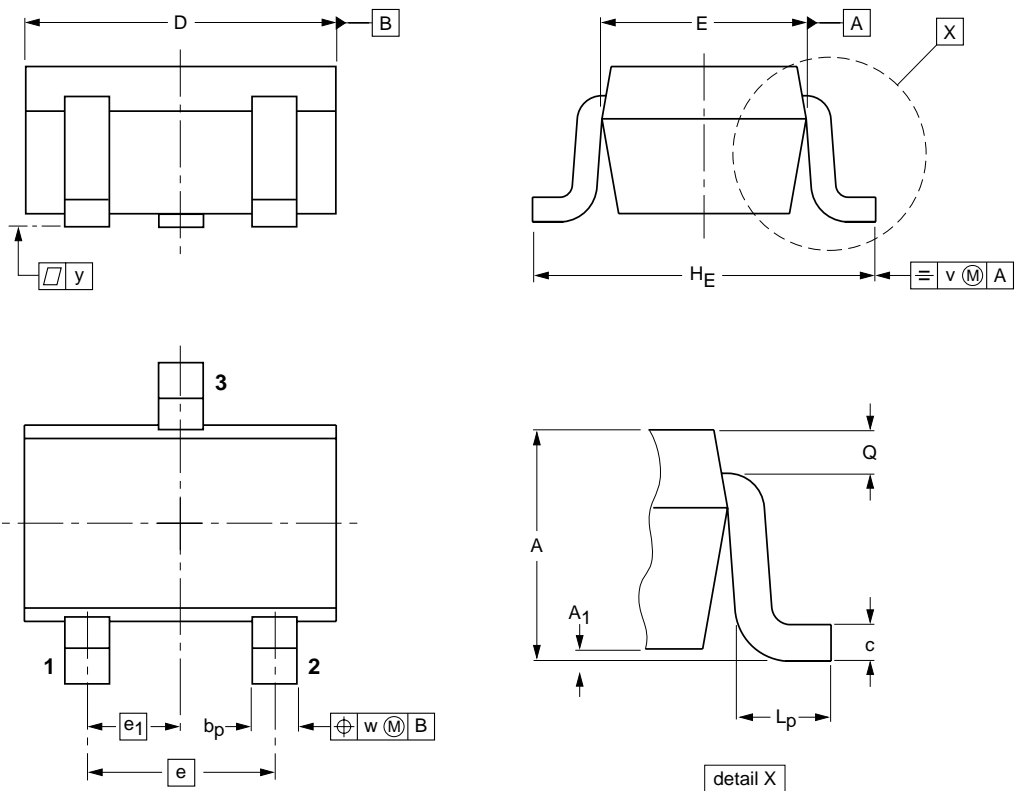
$I_c - V_{BE}$



$P_c - T_a$



■ SOT-323



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ max | b _p | c | D | E | e | e ₁ | H _E | L _p | Q | v | w |
|------|------------|-----------------------|----------------|--------------|------------|--------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.4 0.3 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.23 0.13 | 0.2 | 0.2 |